

Features

- Split Gate Trench MOSFET Technology
- Excellent Package For Heat Dissipation
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device ^(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

**N-CHANNEL
MOSFET**

Maximum Ratings

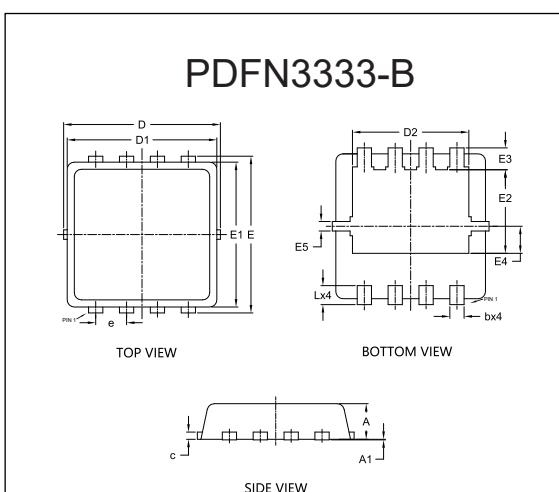
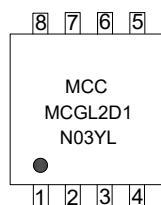
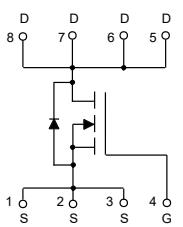
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 50°C/W Junction to Ambient ^(Note2)
- Thermal Resistance: 2.5°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	100	A
T _C =100°C	I _D	63	
Pulsed Drain Current ^(Note3)	I _{DM}	400	A
Total Power Dissipation ^(Note4)	P _D	50	W
Single Pulse Avalanche Energy ^(Note5)	E _{AS}	162	mJ

Note:

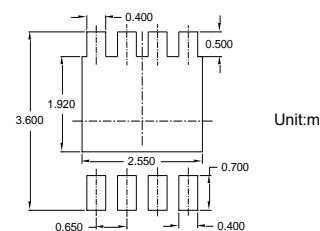
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{DD}=25V, V_{GS}=10V, R_G=25Ω, L=1mH.

Internal Structure and Marking Code



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.028	0.033	0.70	0.85	
A1	0.000	0.002	0.00	0.05	
b	0.008	0.016	0.20	0.40	
c	0.004	0.010	0.10	0.25	
D	0.124	0.136	3.15	3.45	
D1	0.118	0.130	3.00	3.30	
D2	0.089	0.104	2.25	2.65	
E	0.124	0.136	3.15	3.45	
E1	0.114	0.126	2.90	3.20	
E2	0.061	0.076	1.54	1.94	
E3	0.011	0.026	0.28	0.65	
E4	0.022		0.570		TYP
E5	0.008		0.200		TYP
e	0.026		0.650		BSC
L	0.012	0.020	0.300	0.500	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		1.6	2.1	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$		2.5	4.5	
Gate Resistance	R_g	f=1 MHz, Open drain		3		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				100	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=50A$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F=50A, dI_F/dt=100A/\mu s$		52		ns
Reverse Recovery Charge	Q_{rr}			40		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=500KHz$		2630		pF
Output Capacitance	C_{oss}			1830		
Reverse Transfer Capacitance	C_{rss}			100		
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V, I_D=50A$		45		nC
Gate-Source Charge	Q_{gs}			17		
Gate-Drain Charge	Q_{gd}			8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, I_{DS}=50A, R_{GEN}=2.2\Omega$		14		ns
Turn-On Rise Time	t_r			89		
Turn-Off Delay Time	$t_{d(off)}$			27		
Turn-Off Fall Time	t_f			23		

Curve Characteristics

Fig.1 - Typical Output Characteristics

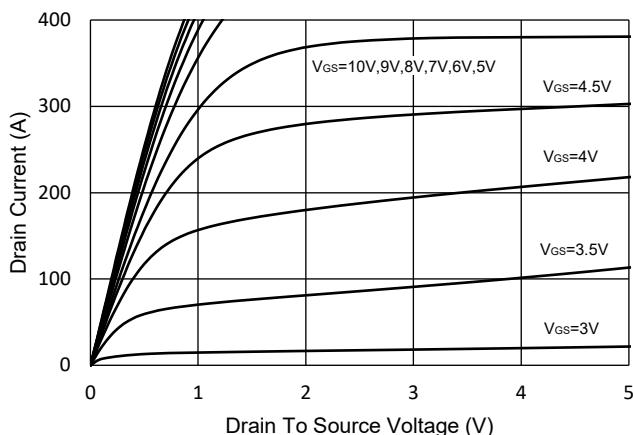


Fig.2 - Transfer Characteristic

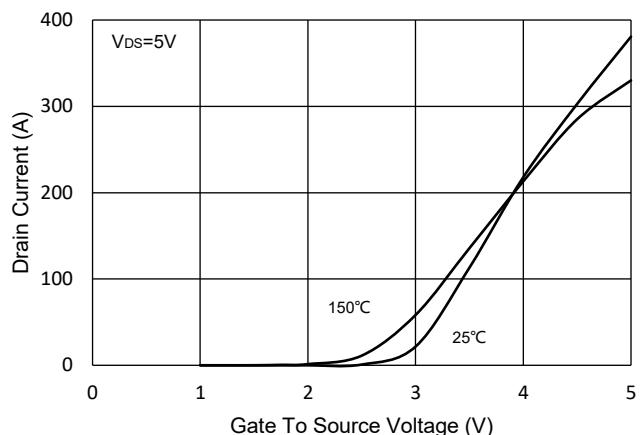


Fig.3 - $R_{DS(ON)}$ - V_{GS}

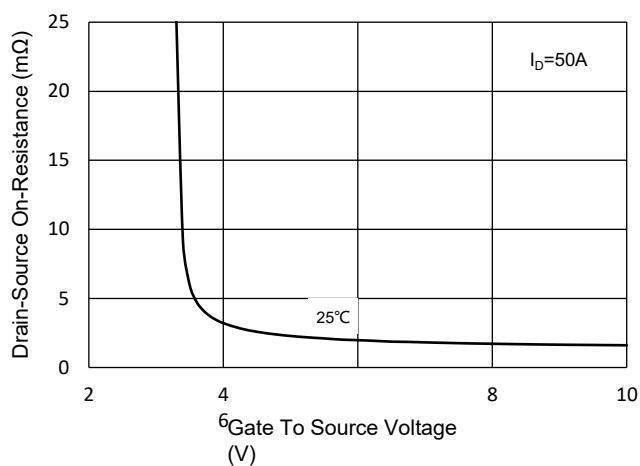


Fig.4 - $R_{DS(ON)}$ - I_D

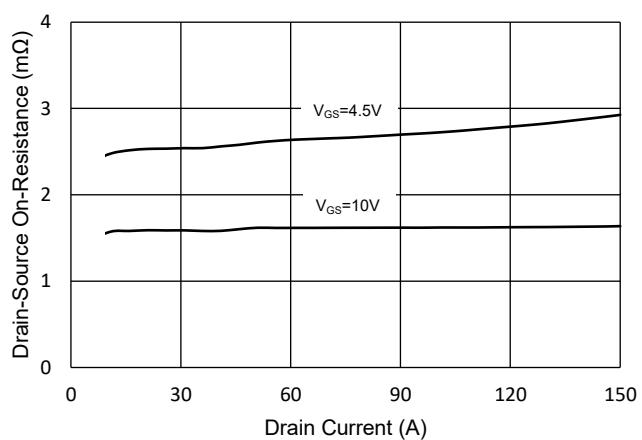


Fig.5 - Capacitance Characteristics

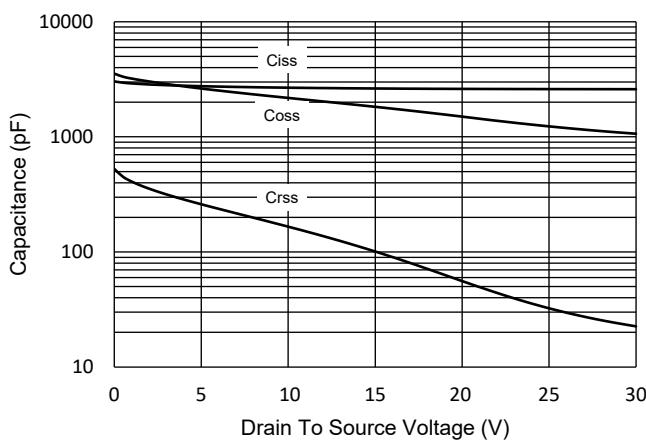
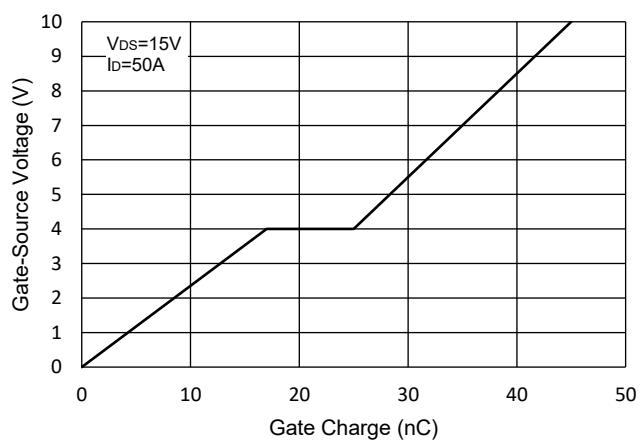


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

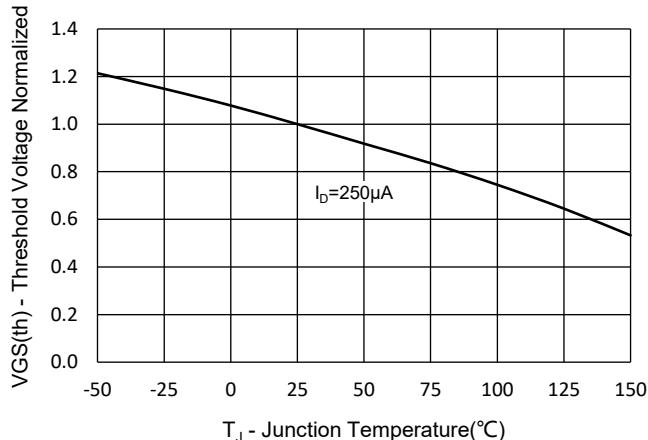


Fig.8 - Normalized On Resistance Characteristics

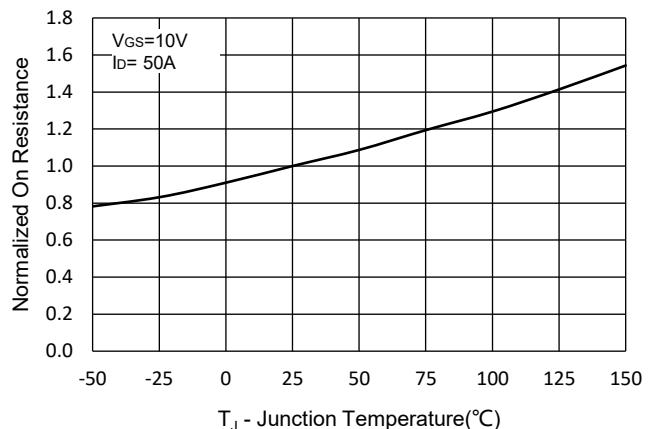


Fig.9 - I_S - V_{SD}

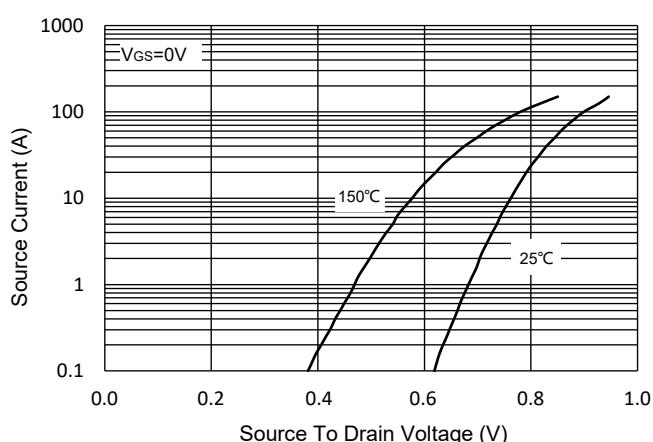


Fig.10 - Drain Current

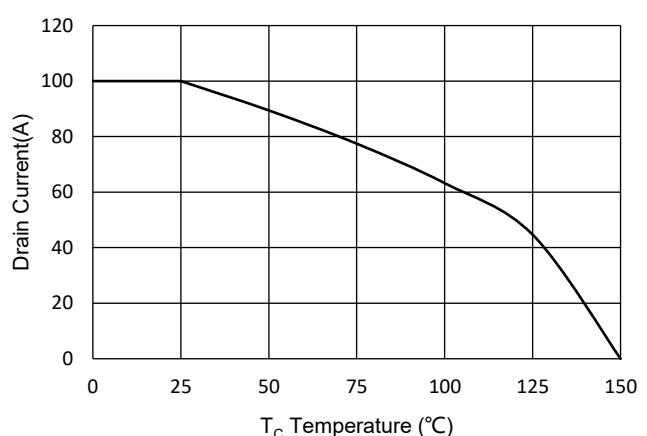
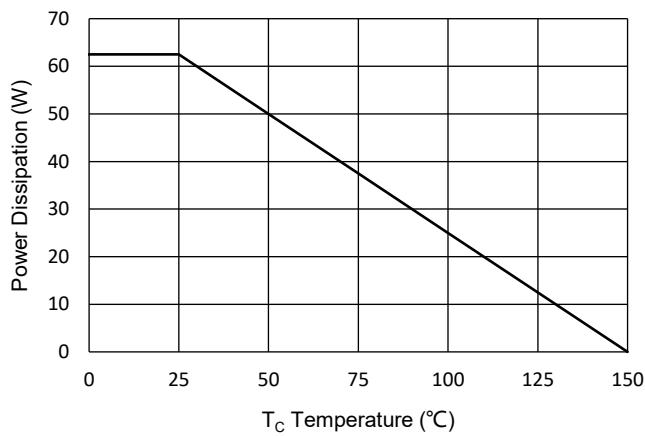


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

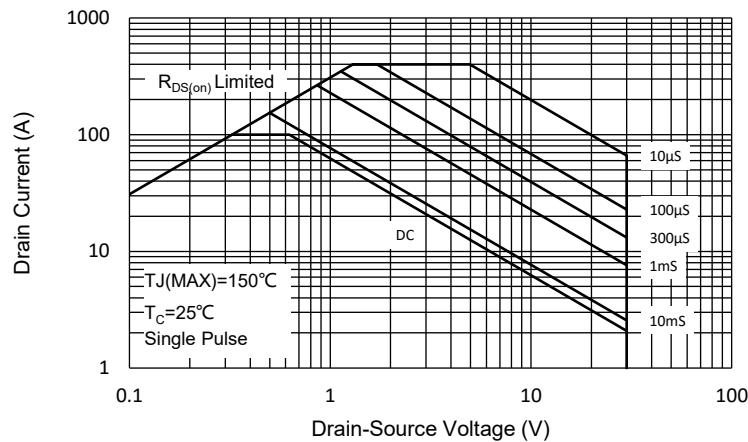
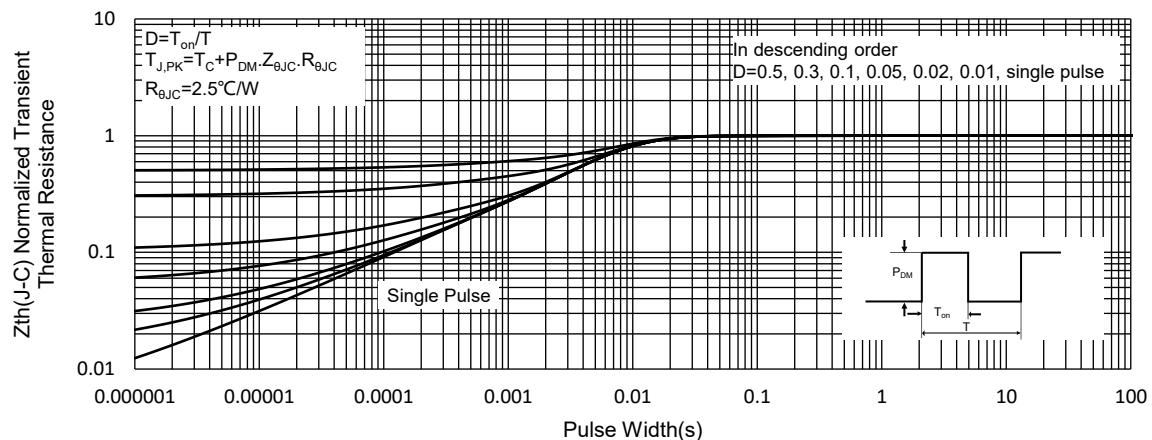


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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